

64M X 72 Bits (512MB) 200-Pin DDR SDRAM SO-DIMM with ECC (PC2100)

FEATURES

- PC2100 Compliant (PC266B 133MHz—7.5ns@CL=2.5)
- 200-Pin SO-DIMM form factor
- SimpleTech Patented IC Tower stacking technology
- Auto and self refresh capability (8192 cycles/64ms refresh)
- SSTL_2 compatible inputs and outputs
- +2.5V ± 0.2V VDD
- DDR architecture: Two data accesses per clock cycle, differential clock inputs (CK0 and /CK0), and bi-directional data strobe (DQS)
- Four internal banks for concurrent operation
- Auto Precharge option for each burst access
- Burst lengths: 2, 4, 8
- All inputs are sampled at the positive going edge of the system clock; data referenced to both edges of DQS
- Serial Presence Detect with EEPROM
- ECC

GENERAL DESCRIPTION

The SimpleTech SL72A8Q64M8M-A75EW is a 64M x 72 bits Double Data Rate (DDR) Synchronous Dynamic RAM (SDRAM) Small-Outline Dual In-line Memory Module (SO-DIMM).

The module consists of eighteen CMOS 8M x 8 bits x 4 banks DDR SDRAMs in 66-pin 400-mil TSOP II packages mounted on a 200-pin glass epoxy substrate in stacks of two using the patented SimpleTech IC Tower stacking technology (Patent Number RE.36,916).

A serial EEPROM using the two pin I²C protocol is also mounted to provide for the Serial Presence Detects (SPD). Decoupling capacitors of 0.22µF are mounted. Damping resistors are mounted for DQ, DQS, and DM signals. A PLL supplies clocks to the SDRAMs from one clock input.

The module has gold edge connections and is intended for mounting into 200-pin SO-DIMM edge connector sockets keyed for 2.5V.

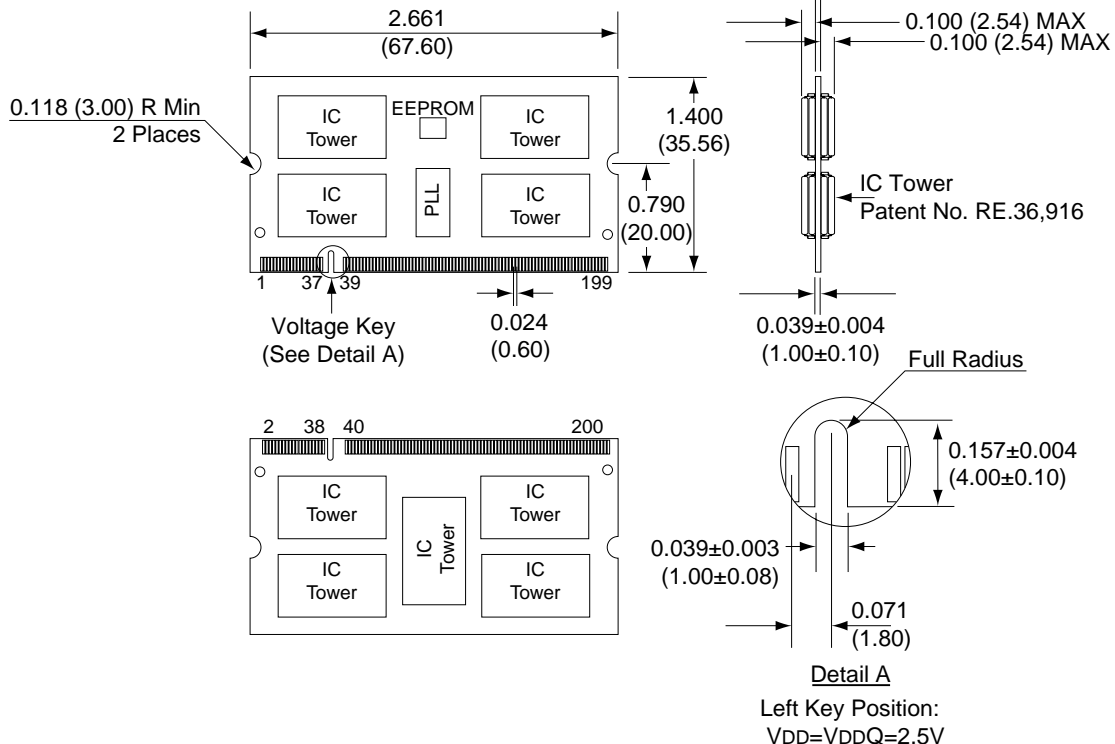
ORDERING INFORMATION

Part Number	CL	MHz	Bandwidth
SL72A8Q64M8M-A75EW	2.5	133	2.1 GB/s

PACKAGE DIMENSIONS

Module Dimensions

Units are in inches (millimeters). Tolerances are ±0.005 (±0.15) unless otherwise specified.

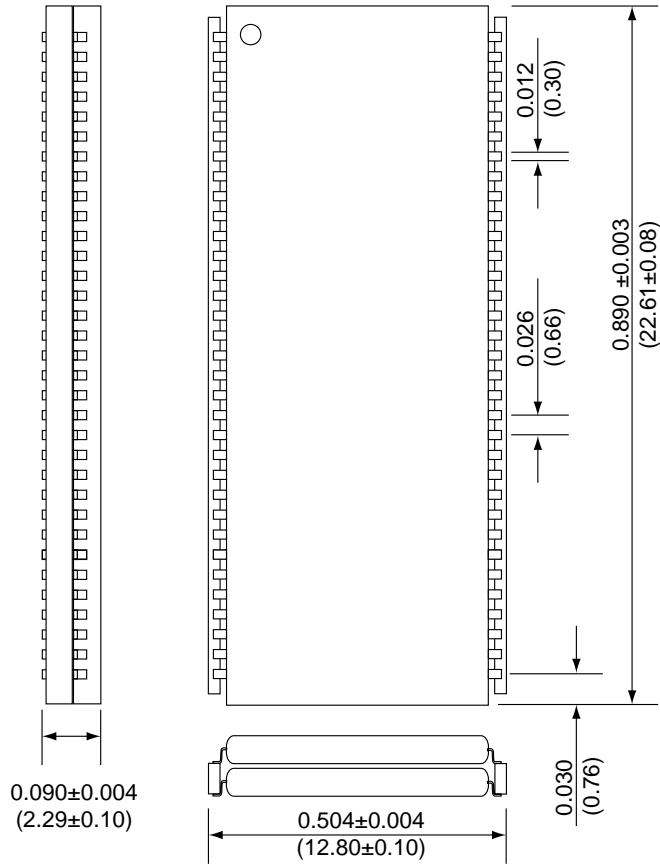


955
(continued)

PACKAGE DIMENSIONS *(continued)*

IC Tower Dimensions

Units are in inches (millimeters). Tolerances are ± 0.005 (± 0.15) unless otherwise specified.



PIN CONFIGURATION (*=Not Used; /=Active Low)

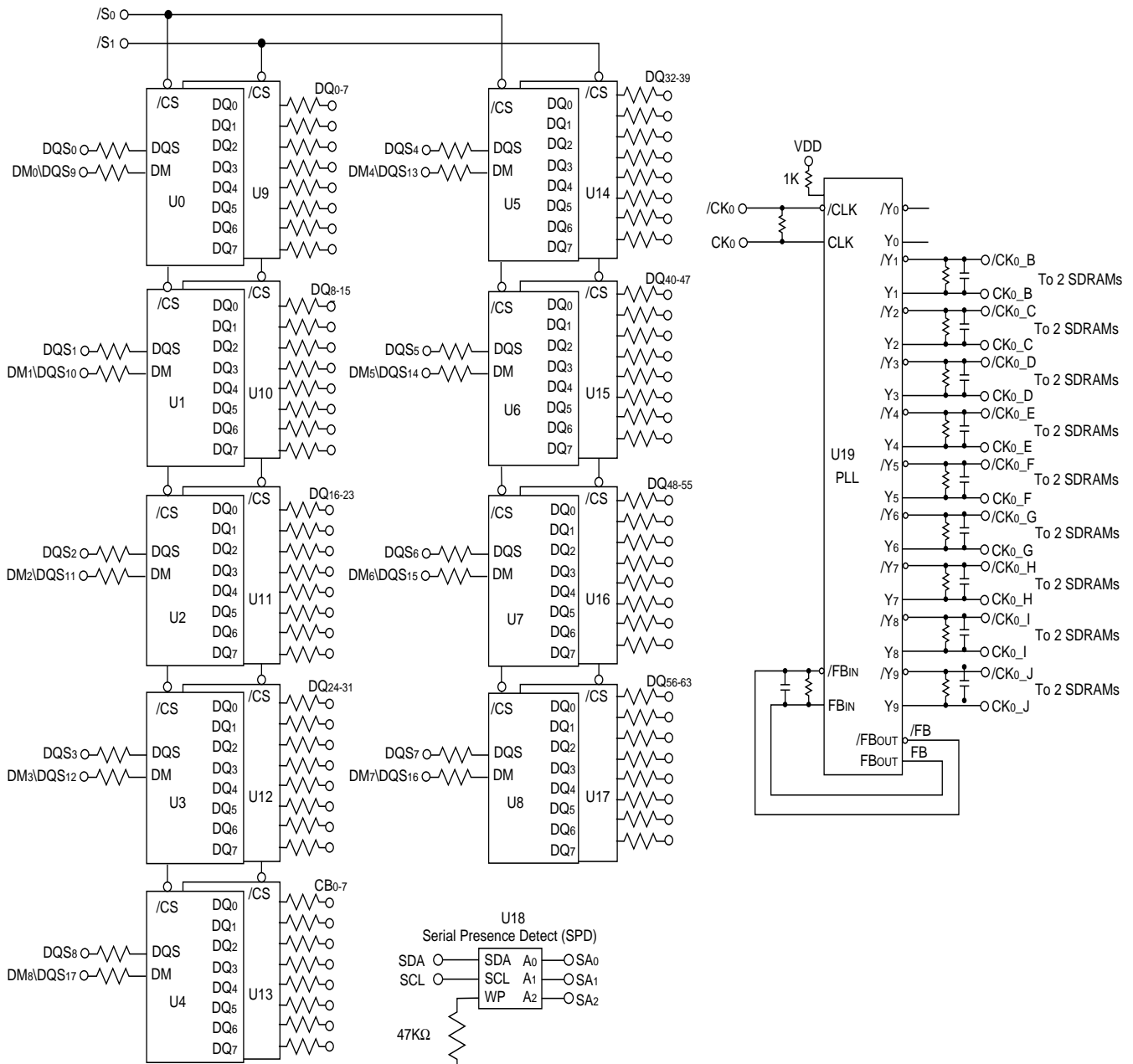
Pinout

Pin	Front	Pin	Back	Pin	Front	Pin	Back	Pin	Front	Pin	Back	Pin	Front	Pin	Back
1	VREF	2	VREF	51	VSS	52	VSS	101	A9	102	A8	151	DQ42	152	DQ46
3	VSS	4	VSS	53	DQ19	54	DQ23	103	VSS	104	VSS	153	DQ43	154	DQ47
5	DQ0	6	DQ4	55	DQ24	56	DQ28	105	A7	106	A6	155	VDD	156	VDD
7	DQ1	8	DQ5	57	VDD	58	VDD	107	A5	108	A4	157	VDD	158	/CK1*
9	VDD	10	VDD	59	DQ25	60	DQ29	109	A3	110	A2	159	VSS	160	CK1*
11	DQS0	12	DM0/DQS9	61	DQS3	62	DM3/DQS12	111	A1	112	A0	161	VSS	162	VSS
13	DQ2	14	DQ6	63	VSS	64	VSS	113	VDD	114	VDD	163	DQ48	164	DQ52
15	VSS	16	VSS	65	DQ26	66	DQ30	115	A10/AP	116	BA1	165	DQ49	166	DQ53
17	DQ3	18	DQ7	67	DQ27	68	DQ31	117	BA0	118	/RAS	167	VDD	168	VDD
19	DQ8	20	DQ12	69	VDD	70	VDD	119	/WE	120	/CAS	169	DQS6	170	DM6/DQS15
21	VDD	22	VDD	71	CB0	72	CB4	121	/S0	122	/S1	171	DQ50	172	DQ54
23	DQ9	24	DQ13	73	CB1	74	CB5	123	DU	124	DU	173	VSS	174	VSS
25	DQS1	26	DM1/DQS10	75	VSS	76	VSS	125	VSS	126	VSS	175	DQ51	176	DQ55
27	VSS	28	VSS	77	DQS8	78	DM8/DQS17	127	DQ32	128	DQ36	177	DQ56	178	DQ60
29	DQ10	30	DQ14	79	CB2	80	CB6	129	DQ33	130	DQ37	179	VDD	180	VDD
31	DQ11	32	DQ15	81	VDD	82	VDD	131	VDD	132	VDD	181	DQ57	182	DQ61
33	VDD	34	VDD	83	CB3	84	CB7	133	DQS4	134	DM4/DQS13	183	DQS7	184	DM7/DQS16
35	CK0	36	VDD	85	DU	86	DU(/RESET)	135	DQ34	136	DQ38	185	VSS	186	VSS
37	/CK0	38	VSS	87	VSS	88	VSS	137	VSS	138	VSS	187	DQ58	188	DQ62
39	VSS	40	VSS	89	CK2*	90	VSS	139	DQ35	140	DQ39	189	DQ59	190	DQ63
41	DQ16	42	DQ20	91	/CK2*	92	VDD	141	DQ40	142	DQ44	191	VDD	192	VDD
43	DQ17	44	DQ21	93	VDD	94	VDD	143	VDD	144	VDD	193	SDA	194	SA0
45	VDD	46	VDD	95	CKE1	96	CKE0	145	DQ41	146	DQ45	195	SCL	196	SA1
47	DQS2	48	DM2/DQS11	97	DU(A13)	98	DU(BA2)	147	DQS5	148	DM5/DQS14	197	VDDSPD	198	SA2
49	DQ18	50	DQ22	99	A12	100	A11	149	VSS	150	VSS	199	VDDID*	200	DU

Pin Description

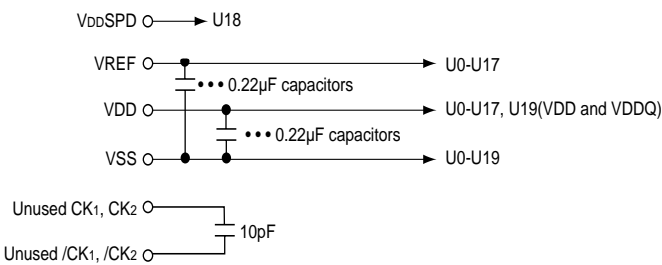
Pin Symbol	Pin Function	Pin Symbol	Pin Function
CK(0:2)	Clock inputs, positive line	DQ(0:63)	Data input/output
/CK(0:2)	Clock inputs, negative line	CB(0:7)	Data check bits input/output
CKE(0:1)	Clock enables	DM(0:8)/DQS(9:17)	Low data masks/high data strobes
/RAS	Row address strobe	DQS(0:8)	Low data strobes
/CAS	Column address strobe	/RESET	Register initialization
/WE	Write enable	VDD	Core power
/S(0:1)	Chip selects	VSS	Ground
A(0:9,11:13)	Address inputs	VREF	Input/output reference
A10/AP	Address input/Autoprecharge	VDDSPD	SPD power
BA(0:2)	SDRAM bank address	VDDID	VDD identification flag
SCL	SPD clock input		
SDA	SPD data input/output	DU	Don't Use
SA(0:2)	SPD address		

FUNCTIONAL BLOCK DIAGRAM



- A0-A10/AP, A11, A12 ○ → A0-A10/AP, A11, A12: SDRAMs U0-U17
- BA0, BA1 ○ → BA0, BA1: SDRAMs U0-U17
- /RAS ○ → /RAS: SDRAMs U0-U17
- /CAS ○ → /CAS: SDRAMs U0-U17
- /WE ○ → /WE: SDRAMs U0-U17
- CKE0 ○ → CKE: SDRAMs U0-U8
- CKE1 ○ → CKE: SDRAMs U9-U17

Notes: 1. Unless otherwise noted, all series resistors are 22Ω.
 2. DQ wiring may differ from that described in this drawing; however DQ, DQS, DM, CKE, and /S relationships are maintained as shown.



SERIAL PRESENCE DETECT INFORMATION

Serial PD Interface Protocol: I²C; Current sink capability of SDA driver - 3mA; Maximum clock frequency: 100 KHz

Byte #	Function Described	Function Supported	Hex Value
		PC266B	PC266B
0	# of bytes written into serial memory at module manufacturer	128 bytes	80h
1	Total # of bytes of SPD memory device	256Bytes (2K-bit)	08h
2	Fundamental memory type	DDR SDRAM	07h
3	# of row addresses on this assembly	13	0Dh
4	# of column addresses on this assembly	10	0Ah
5	# of physical banks on this assembly	2 banks	02h
6	Data width of this assembly	72 bits	48h
7	...Data width of this assembly (continued)	—	00h
8	Voltage interface level of this assembly	SSTL 2.5V	04h
9	SDRAM cycle time at CL=2.5 (tCYC)	7.5ns	75h
10	SDRAM access time from clock at CL=2.5 (tAC)	0.75ns	75h
11	DIMM configuration type	ECC	02h
12	Refresh rate/type	7.8µs, Self -refresh	82h
13	SDRAM width	8 bits	08h
14	Error Checking SDRAM data width	8 bits	08h
15	Min. CLK delay for back-to-back rand. col. addr.	tCCD=1 CLK	01h
16	SDRAM device attributes: burst lengths supported	2,4,8	0Eh
17	SDRAM device attributes: # of banks on SDRAM device	4 banks	04h
18	SDRAM device attributes: CAS latency	CAS latency = 2.0, 2.5	0Ch
19	SDRAM device attributes: CS latency	CS latency = 0	01h
20	SDRAM device attributes: Write latency	Write Latency = 1	02h
21	SDRAM module attributes	Differential clock, PLL	24h
22	SDRAM device attributes: general	VDD±0.2V	00h
23	Minimum clock cycle time at CL=2 (tCYC)	8ns	80h
24	Max. data access time form clock at CL=2 (tAC)	0.75ns	75h
25	Minimum clock cycle time at CL=1.5 (tCYC)	N/A	00h
26	Max. data access time from clock at CL=1.5 (tAC)	N/A	00h
27	Minimum row precharge time (tRP)	20.0ns	50h
28	Minimum row active to row active delay (tRRD)	15.0ns	3Ch
29	Minumum RAS to CAS (tRCD)	20.0ns	50h
30	Minumum RAS pulse width (tRAS)	45ns	2Dh
31	Module bank density	256MB	40h
32	Min. command and address signal setup time (tAS)	1.1ns	E0h
33	Min. command and address signal hold time (tAH)	1.1ns	E0h
34	Min. data/data mask signal input setup time (tDS)	0.5ns	50h
35	Min. data/data mask signal input hold time (tDH)	0.5ns	50h

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Byte #	Function Described	Function Supported	Hex Value
		PC266B	PC266B
36-61	Superset information (may be used in future)	no superset	00h
62	SPD revision	JEDEC 1	00h
63	Checksum for bytes 0-62	JEDEC calculation	xxh
64	Manufacturer's JEDEC ID code per JEP-106E	Continuation code	7Fh
65	Man. JEDEC ID code (continued)	SimpleTech's ID	A8h
66-71			00h
72	Manufacturing location	SimpleTech USA	01h
73-90	Manufacturer's part number		xxh
91	Revision code of PCB	Eng(00),RevA(01),RevB(02)	01h
92			00h
93	Manufacturing date	Year (BCD)	yy
94		Calender Week (BCD)	ww
95	Assembly serial number	Tester number	ss
96		Serial number (bits 7-0)	ss
97		Serial number (bits 15-8)	ss
98		Serial number (bits 23-16)	ss
99-127	Manufacture's specific data		xxh
128-255		Undefined	00h